TOSHIBA TRANSISTOR SILICON NPN TRIPLE DIFFUSED TYPE

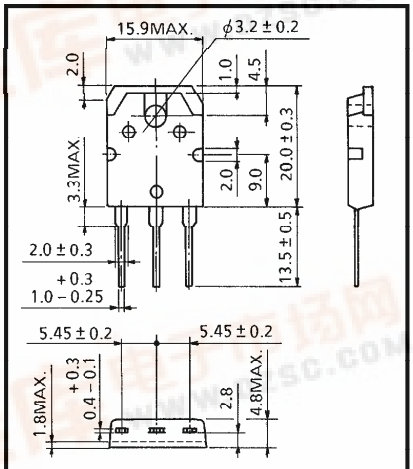
2SC2792

SWITCHING REGULATOR AND HIGH VOLTAGE SWITCHING APPLICATIONS.

HIGH SPEED DC-DC CONVERTER APPLICATIONS.

INDUSTRIAL APPLICATIONS

Unit in mm



1. BASE
2. COLLECTOR (HEAT SINK)
3. EMITTER

JEDEC	—
EIAJ	—
TOSHIBA	2-16B1A

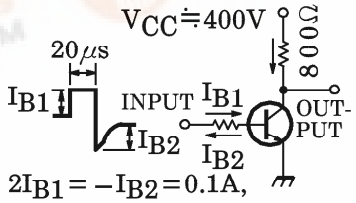
Weight : 4.6g

- Excellent Switching Times (I_C = 0.5A)
  t_r = 1.0μs Max. t_f = 1.0μs Max.
- High Collector Breakdown Voltage : V_{CEO} = 800V

MAXIMUM RATINGS (Ta = 25°C)

CHARACTERISTIC		SYMBOL	RATING	UNIT
Collector-Base Voltage		V_{CBO}	850	V
Collector-Emitter Voltage		V_{CEO}	800	V
Emitter-Base Voltage		V_{EBO}	7	V
Collector Current	DC	I_C	2	A
	Pulse	I_{CP}	4	A
Base Current		I_B	1	A
Collector Power Dissipation (Tc = 25°C)		P_C	80	W
Junction Temperature		T_j	150	°C
Storage Temperature Range		T_{stg}	−55~150	°C

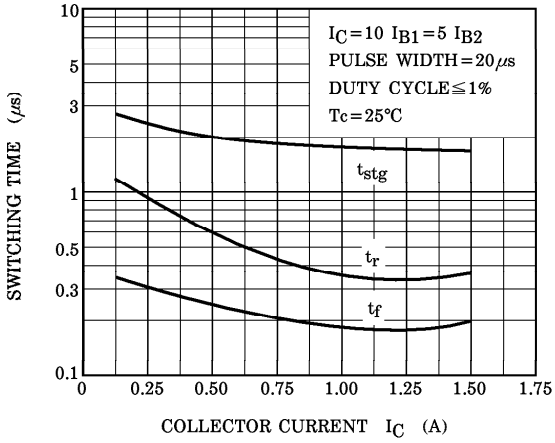
ELECTRICAL CHARACTERISTICS (Ta = 25°C)

CHARACTERISTIC		SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Collector Cut-off Current		I_{CBO}	V_{CB} = 800V, I_E = 0	—	—	100	μA
Emitter Cut-off Current		I_{EBO}	V_{EB} = 7V, I_C = 0	—	—	1	mA
Collector-Base Breakdown Voltage		$V_{(BR)CBO}$	I_C = 1mA, I_E = 0	850	—	—	V
Collector-Emitter Breakdown Voltage		$V_{(BR)CEO}$	I_C = 10mA, I_B = 0	800	—	—	V
DC Current Gain		h_{FE}	V_{CE} = 5V, I_C = 0.5A	10	—	—	
Saturation Voltage	Collector-Emitter	$V_{CE(sat)}$	I_C = 0.5A, I_B = 0.05A	—	—	1.0	V
	Base-Emitter	$V_{BE(sat)}$	I_C = 0.5A, I_B = 0.05A	—	—	1.5	V
Switching Time	Rise Time	t_r		—	—	1.0	μs
	Storage Time	t_{stg}		—	—	4.0	
	Fall Time	t_f		—	—	1.0	

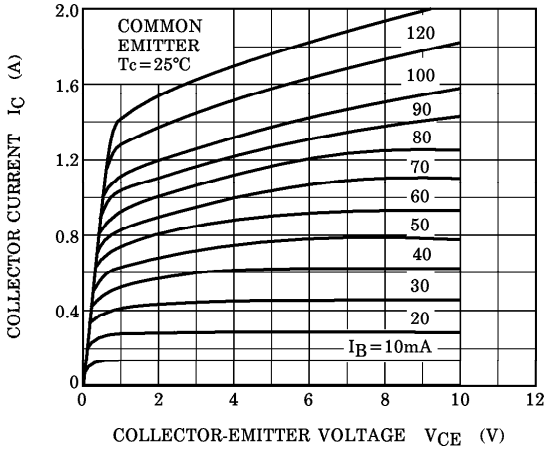
$2I_{B1} = -I_{B2}$ = 0.1A,
DUTY CYCLE ≦ 1%

961001EAA2

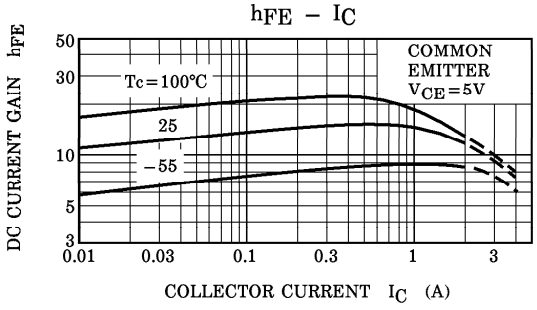
SWITCHING TIME – I_C



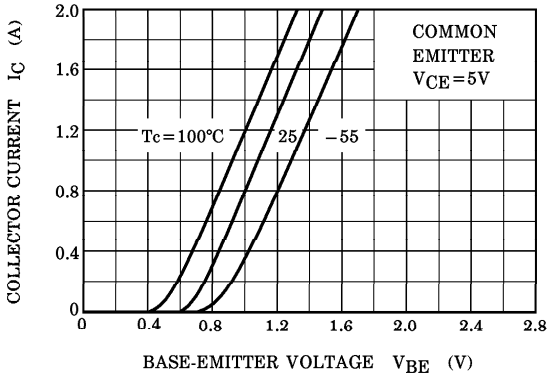
I_C – V_{CE}



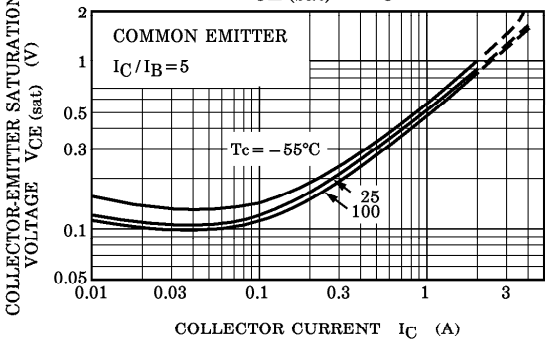
h_{FE} – I_C



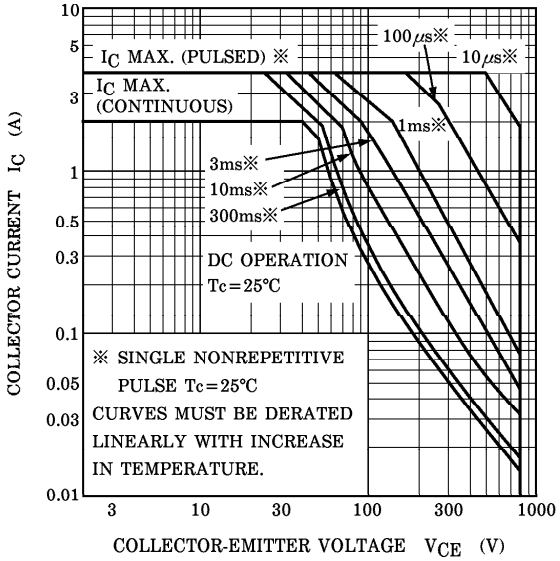
I_C – V_{BE}



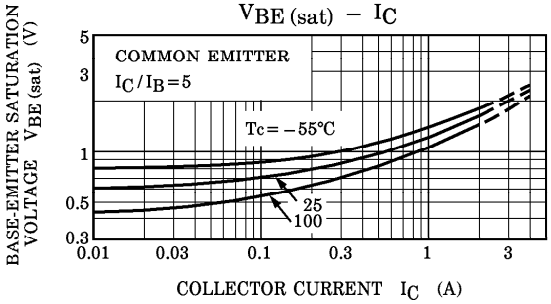
$V_{CE(sat)}$ – I_C



SAFE OPERATING AREA



$V_{BE(sat)}$ – I_C



961001EAA2'